

S13 2	911	(projection near2 exposure) and stepper and (optical near2 element)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/11 16:48
S13 3	791	S132 and substrate and pattern	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/11 17:17
S13 4	0	S132 and "248"/\$3 and 250/3\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/11 18:35
S13 5	67300	gate near2 oxide	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/11 18:35
S13 6	2156	S135 and (electron near2 beam)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/11 18:35
S13 7	129	S136 and (dielectric near2 breakdown)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/11 18:57
S13 8	22	S136 and (dielectric near2 breakdown) and cathode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/11 19:01
S13 9	8	fei and dualbeam	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/11 19:08

S14 0	57	fei and (electron near2 gun)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/11 19:11
S14 1	4	fei and (electron near2 gun) and dualbeam	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/11 19:53
S14 2	0	fei and (electron near2 gun) and dualbeam and "820"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/11 19:53

L17	8	I15 and dielectric near2 breakdown	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/12 14:43
L18	74	sem and (decelerat\$3 near3 field) and objective	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/12 17:01
L19	70	I18 and (objective near3 lens)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/12 17:02
S1	56767	ion near2 beam	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/26 15:52
S2	6171	S1 and (beam near3 current)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/02 12:31
S3	0	S2 and (processinf near2 beam) and (edge near2 process\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/02 12:32
S4	10	S2 and (processing near2 beam) and (edge near2 process\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/02 12:51
S5	56	"4503329"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/02 12:51

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	0	(defect near2 failure) and (small near2 dose\$3) and (electron near2 beam)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/12 12:34
L2	6	(dielectric near3 breakdown) and (small near2 dose\$3) and (electron near2 beam)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/12 12:37
L3	0	(dielectric near3 defect) and (small near2 dose\$3) and (electron near2 beam)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/12 12:37
L4	0	(dielectric near3 failure) and (small near2 dose\$3) and (electron near2 beam)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/12 12:38
L5	200	(dielectric near3 (breakdown failure)) and (dose\$3) and (electron near2 beam)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/12 12:38
L6	20	(dielectric near3 (breakdown failure)) and (dose\$3) and (electron near2 beam) and sem	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/12 12:52
L7	70	(different near2 dose\$3) and (electron near2 beam) and sem	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/12 14:22
L8	8202	YANAGI	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/05/12 13:18